N-Channel 150-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

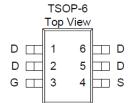
Typical Applications:

- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)	
150	1100 @ V _{GS} = 10V	1.1	
	1300 @ V _{GS} = 4.5V	1.0	









ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Limit	Units	
Drain-Source Voltage			150	V	
Gate-Source Voltage			±20		
Continuous Drain Coursent®	T _A =25°C		1.1		
Continuous Drain Current a	T _A =70°C	l _D	0.9	Α	
Pulsed Drain Current ^b			10		
Continuous Source Current (Diode Conduction) ^a		I _S	1.7	Α	
Device Discipation 8	T _A =25°C	D	2	W	
Power Dissipation ^a	T _A =70°C	P _D	1.3	VV	
Operating Junction and Storage Temperature Range		T_J , T_{stg}	-55 to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter			Maximum	Units		
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	62.5	°C/W		
Maximum Junction-to-Ambient	Steady State	IXOJA	110	C/VV		

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

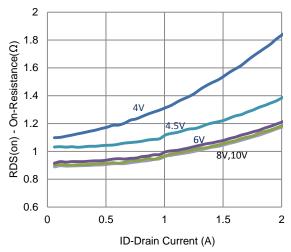
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±10	uA	
Zero Gate Voltage Drain Current	1	$V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zero Gate Voltage Brain Current	I _{DSS}	$V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$		25		uA	
On-State Drain Current	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	5			Α	
Drain-Source On-Resistance	r	$V_{GS} = 10 \text{ V}, I_D = 1.1 \text{ A}$			1100	mΩ	
Dialii-Source Off-Resistance	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 1 \text{ A}$			1300		
Forward Transconductance	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 1.1 \text{ A}$		10		S	
Diode Forward Voltage	V_{SD}	$I_S = 0.9 \text{ A}, V_{GS} = 0 \text{ V}$		0.82		V	
		Dynamic					
Total Gate Charge	Q_g			3.2			
Gate-Source Charge	Q_{gs}	$V_{DS} = 75 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 1.1 \text{ A}$		1.0		nC	
Gate-Drain Charge	Q_gd			1.9			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 75 \text{ V}, R_{L} = 68 \Omega,$		4			
Rise Time	t _r	$V_{DS} = 75 \text{ V}, R_L - 66 \Omega,$ $I_D = 1.1 \text{ A},$		5		no	
Turn-Off Delay Time	t _{d(off)}	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		20		ns	
Fall Time	t _f	V GEN - 10 V, NGEN - 0 12		7			
Input Capacitance	C _{iss}			179			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		14		pF	
Reverse Transfer Capacitance	C_{rss}			12			

Notes

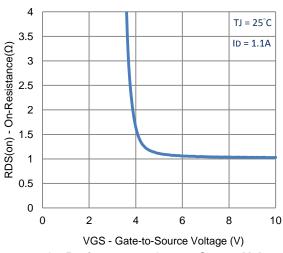
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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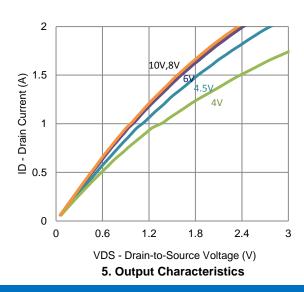
Typical Electrical Characteristics

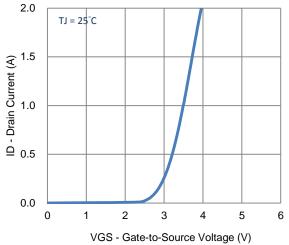


1. On-Resistance vs. Drain Current

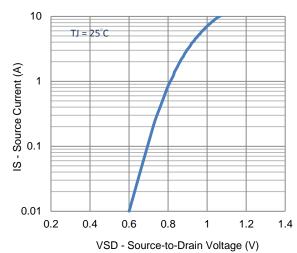


3. On-Resistance vs. Gate-to-Source Voltage

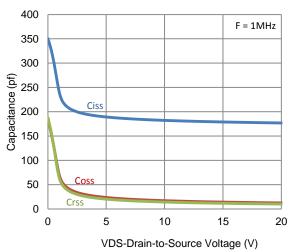




2. Transfer Characteristics

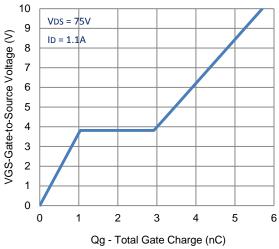


4. Drain-to-Source Forward Voltage

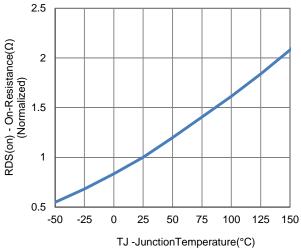


6. Capacitance

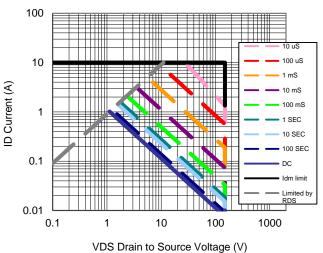
Typical Electrical Characteristics



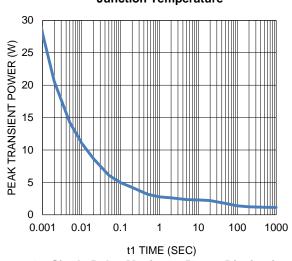
7. Gate Charge (nc)



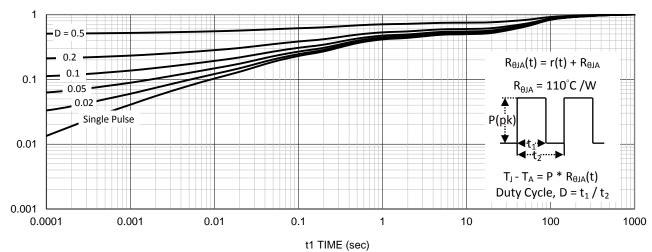
8. Normalized On-Resistance Vs Junction Temperature



9. Safe Operating Area

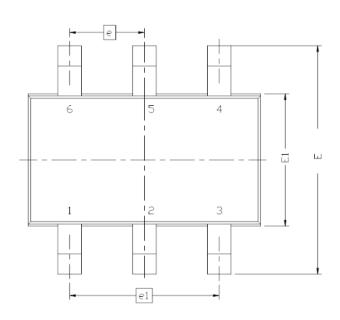


10. Single Pulse Maximum Power Dissipation

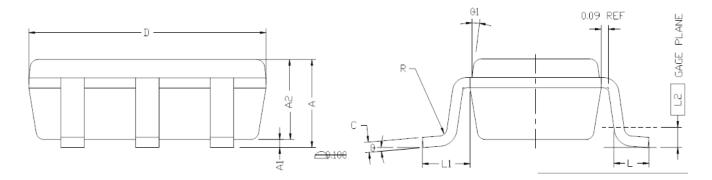


11. Normalized Thermal Transient Junction to Ambient

Package Information



DIM.	MILLIMETERS					
DIM	MIN	NDM	MAX			
Α	0.935		1.10			
A1	0.01		0.10			
A2	0.70		1.00			
b	0.25	0.32	0.40			
C	0.10	0.15	0.20			
D	2.95	3.05	3.10			
Ε	2.70	2.85	2.98			
E1	1.55	1.65	1.70			
6	0.95 BSC					
L	0.30		0.60			
L1	0.60REF					
T5	0.25BSC					
R	0.10					
θ	0?	4?	8?			
θ1	7? N□M					



Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Tie Bar Burrs, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.
- 4. The Package Top May Be Smaller Than The Package Bottom.
- 5. Dimension "B" Does Not Include Dambar Protrusion. Allowable Dambar Protrusion Shall Be 0.08 mm Total In Excess Of "B" Dimension At Maximum Material Condition. The Dambar Cannot Be Located On The Lower Radius Of The Foot.